Верифікація





[117] Evstigneev S.V. 8th Int. Symp."Nanostructures: Physics and *Technology*". St Peterburg, Russia, June 19–23, 2000. – P. 494–497.



[3] S. Suzuki et. al., "Fundamental oscillation of resonant tunneling diodes above 1 THz at room temperature", Appl. *Phys. Lett.*, vol.97, no.24, pp. 242102-242102-3, Dec. 2010

РТД 1 [67] (*MBE*)



Ni/Au/Ge i-AlAs i-GaAs *n*-GaAs

[67] Boykin T.B. Resonant tunneling diodes with emitter prewells / T.B. Boykin, R.C. Bowen, G. Klimeck // Appl. Phys. Lett. - 1999. - Vol. 75. - P. 1302-1304.









[113] Yatskiv R. Analysis of the resonant tunneling diode with the stepped pre-barrier / R. Yatskiv, J. Voves // Journal of physics: conference series. – 2009. – Vol. 193. – P. 1–4.

